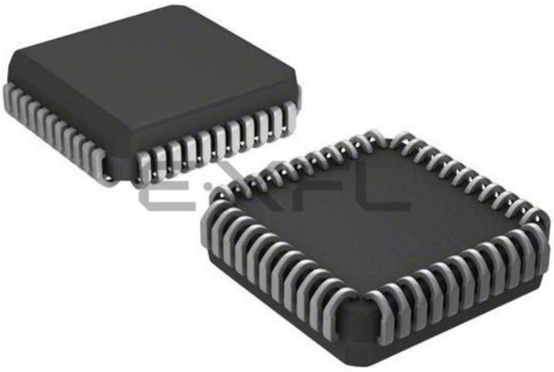

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	PIC
Core Size	8-Bit
Speed	4MHz
Connectivity	I²C, SPI
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	33
Program Memory Size	3.5KB (2K x 14)
Program Memory Type	OTP
EEPROM Size	-
RAM Size	128 x 8
Voltage - Supply (Vcc/Vdd)	2.5V ~ 6V
Data Converters	-
Oscillator Type	External
Operating Temperature	0°C ~ 70°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LCC (J-Lead)
Supplier Device Package	44-PLCC (16.59x16.59)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic16lc64a-04-l

4.2.2.4 PIE1 REGISTER

Applicable Devices													
61	62	62A	R62	63	R63	64	64A	R64	65	65A	R65	66	67

This register contains the individual enable bits for the peripheral interrupts.

Note: Bit PEIE (INTCON<6>) must be set to enable any peripheral interrupt.

FIGURE 4-12: PIE1 REGISTER FOR PIC16C62/62A/R62 (ADDRESS 8Ch)

RW-0	R/W-0	U-0	U-0	R/W-0	R/W-0	R/W-0	R/W-0
—	—	—	—	SSPIE	CCP1IE	TMR2IE	TMR1IE
bit7							bit0

R = Readable bit
W = Writable bit
U = Unimplemented bit, read as ‘0’
- n = Value at POR reset

bit 7-6: **Reserved**: Always maintain these bits clear.

bit 5-4: **Unimplemented**: Read as '0'

bit 3: **SSPIE**: Synchronous Serial Port Interrupt Enable bit
1 = Enables the SSP interrupt
0 = Disables the SSP interrupt

bit 2: **CCP1IE**: CCP1 Interrupt Enable bit
1 = Enables the CCP1 interrupt
0 = Disables the CCP1 interrupt

bit 1: **TMR2IE**: TMR2 to PR2 Match Interrupt Enable bit
1 = Enables the TMR2 to PR2 match interrupt
0 = Disables the TMR2 to PR2 match interrupt

bit 0: **TMR1IE**: TMR1 Overflow Interrupt Enable bit
1 = Enables the TMR1 overflow interrupt
0 = Disables the TMR1 overflow interrupt

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FIGURE 4-17: PIR1 REGISTER FOR PIC16C63/R63/66 (ADDRESS 0Ch)

R/W-0	R/W-0	R-0	R-0	R/W-0	R/W-0	R/W-0	R/W-0
—	—	RCIF	TXIF	SSPIF	CCP1IF	TMR2IF	TMR1IF
bit7							bit0

R = Readable bit
W = Writable bit
U = Unimplemented bit, read as ‘0’
- n = Value at POR reset

bit 7-6: **Reserved:** Always maintain these bits clear.

bit 5: **RCIF:** USART Receive Interrupt Flag bit
1 = The USART receive buffer is full (cleared by reading RCREG)
0 = The USART receive buffer is empty

bit 4: **TXIF:** USART Transmit Interrupt Flag bit
1 = The USART transmit buffer is empty (cleared by writing to TXREG)
0 = The USART transmit buffer is full

bit 3: **SSPIF**: Synchronous Serial Port Interrupt Flag bit
1 = The transmission/reception is complete (must be cleared in software)
0 = Waiting to transmit/receive

bit 2: **CCP1IF**: CCP1 Interrupt Flag bit
<u>Capture Mode</u>
1 = A TMR1 register capture occurred (must be cleared in software)
0 = No TMR1 register capture occurred
<u>Compare Mode</u>
1 = A TMR1 register compare match occurred (must be cleared in software)
0 = No TMR1 register compare match occurred
<u>PWM Mode</u>
Unused in this mode

bit 1: **TMR2IF**: TMR2 to PR2 Match Interrupt Flag bit
1 = TMR2 to PR2 match occurred (must be cleared in software)
0 = No TMR2 to PR2 match occurred

bit 0: **TMR1IF**: TMR1 Overflow Interrupt Flag bit
1 = TMR1 register overflow occurred (must be cleared in software)
0 = No TMR1 register overflow occurred

Interrupt flag bits get set when an interrupt condition occurs regardless of the state of its corresponding enable bit or the global enable bit, GIE (INTCON<7>). User software should ensure the appropriate interrupt flag bits are clear prior to enabling an interrupt.

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5.6 I/O Programming Considerations

Applicable Devices													
61	62	62A	R62	63	R63	64	64A	R64	65	65A	R65	66	67

5.6.1 BI-DIRECTIONAL I/O PORTS

Any instruction which writes, operates internally as a read followed by a write operation. The `BCF` and `BSF` instructions, for example, read the register into the CPU, execute the bit operation and write the result back to the register. Caution must be used when these instructions are applied to a port with both inputs and outputs defined. For example, a `BSF` operation on bit5 of PORTB will cause all eight bits of PORTB to be read into the CPU. Then the `BSF` operation takes place on bit5 and PORTB is written to the output latches. If another bit of PORTB is used as a bi-directional I/O pin (e.g., bit0) and it is defined as an input at this time, the input signal present on the pin itself would be read into the CPU and rewritten to the data latch of this particular pin, overwriting the previous content. As long as the pin stays in the input mode, no problem occurs. However, if bit0 is switched into output mode later on, the content of the data latch may now be unknown.

Reading the port register, reads the values of the port pins. Writing to the port register writes the value to the port latch. When using read-modify-write instructions (ex. `BCF, BSF`, etc.) on a port, the value of the port pins is read, the desired operation is done to this value, and this value is then written to the port latch.

Example 5-4 shows the effect of two sequential read-modify-write instructions on an I/O port.

EXAMPLE 5-4: READ-MODIFY-WRITE INSTRUCTIONS ON AN I/O PORT

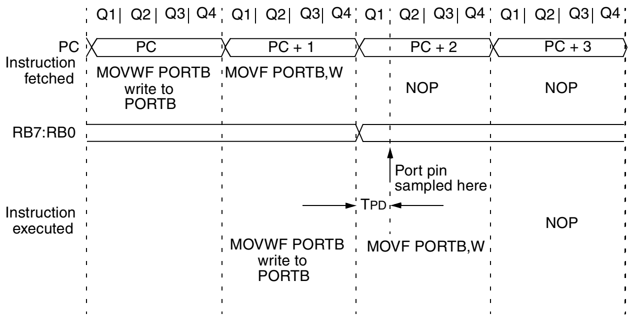
```
;Initial PORT settings: PORTB<7:4> Inputs
;                       PORTB<3:0> Outputs
;PORTB<7:6> have external pull-ups and are
;not connected to other circuitry
;
;                    PORT latch  PORT pins
;                    ----------  ---------
  BCF PORTB, 7     ; 01pp pppp   11pp pppp
  BCF PORTB, 6     ; 10pp pppp   11pp pppp
  BSF STATUS, RP0  ;
  BCF TRISB, 7     ; 10pp pppp   11pp pppp
  BCF TRISB, 6     ; 10pp pppp   10pp pppp
;
;Note that the user may have expected the
;pin values to be 00pp pppp. The 2nd BCF
;caused RB7 to be latched as the pin value
;(high).
```

A pin actively outputting a Low or High should not be driven from external devices at the same time in order to change the level on this pin (“wired-or”, “wired-and”). The resulting high output currents may damage the chip.

5.6.2 SUCCESSIVE OPERATIONS ON I/O PORTS

The actual write to an I/O port happens at the end of an instruction cycle, whereas for reading, the data must be valid at the beginning of the instruction cycle (Figure 5-10). Therefore, care must be exercised if a write followed by a read operation is carried out on the same I/O port. The sequence of instructions should be such to allow the pin voltage to stabilize (load dependent) before the next instruction which causes that file to be read into the CPU is executed. Otherwise, the previous state of that pin may be read into the CPU rather than the new state. When in doubt, it is better to separate these instructions with a `NOP` or another instruction not accessing this I/O port.

FIGURE 5-10: SUCCESSIVE I/O OPERATION



Note:

This example shows a write to PORTB followed by a read from PORTB.

Note that:

data setup time = (0.25T_{CY} - T_{PD})

where T_{CY} = instruction cycle
T_{PD} = propagation delay

Therefore, at higher clock frequencies, a write followed by a read may be problematic.

Figure 11-19 and Figure 11-20 show Master-transmitter and Master-receiver data transfer sequences.

When a master does not wish to relinquish the bus (by generating a STOP condition), a repeated START condition (Sr) must be generated. This condition is identical to the start condition (SDA goes high-to-low while SCL is high), but occurs after a data transfer acknowledge pulse (not the bus-free state). This allows a master to send “commands” to the slave and then receive the requested information or to address a different slave device. This sequence is shown in Figure 11-21.

FIGURE 11-19: MASTER-TRANSMITTER SEQUENCE

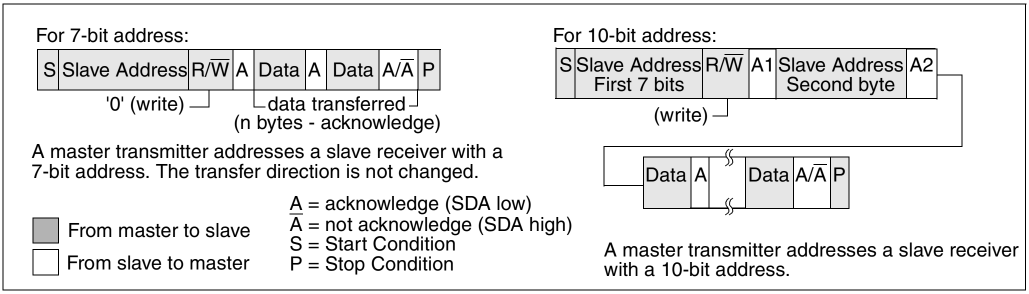


FIGURE 11-20: MASTER-RECEIVER SEQUENCE

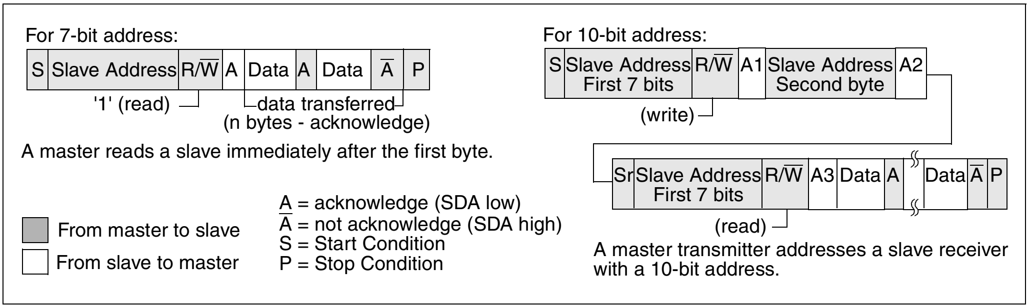
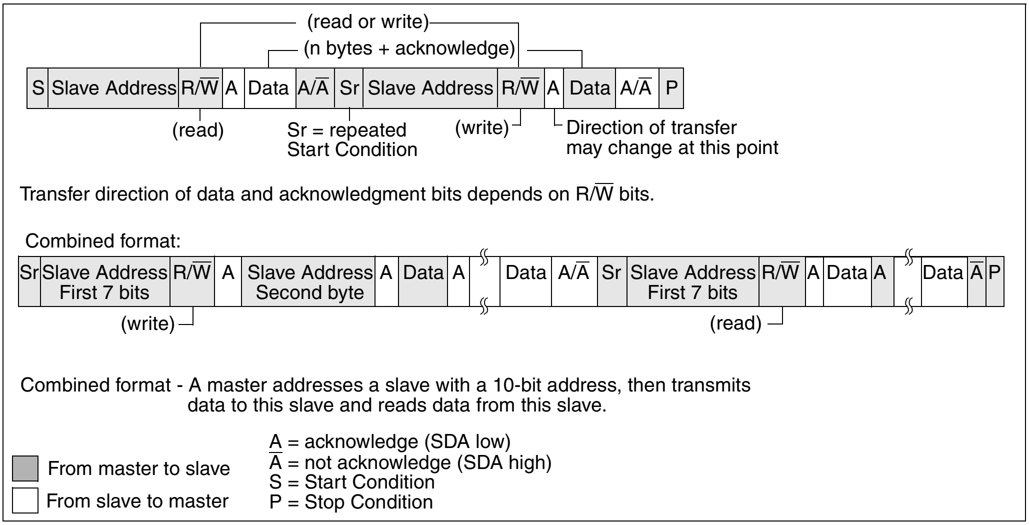


FIGURE 11-21: COMBINED FORMAT



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13.3 Reset

Applicable Devices													
61	62	62A	R62	63	R63	64	64A	R64	65	65A	R65	66	67

The PIC16CXX differentiates between various kinds of reset:

- Power-on Reset (POR)
- $\overline{\text{MCLR}}$ reset during normal operation
- $\overline{\text{MCLR}}$ reset during SLEEP
- WDT Reset (normal operation)
- Brown-out Reset (BOR) - Not on PIC16C61/62/64/65

Some registers are not affected in any reset condition, their status is unknown on POR and unchanged in any other reset. Most other registers are reset to a "reset state" on Power-on Reset (POR), on $\overline{\text{MCLR}}$ or WDT Reset, on $\overline{\text{MCLR}}$ reset during SLEEP, and on Brown-out Reset (BOR). They are not affected by a WDT Wake-up, which is viewed as the resumption of normal operation.

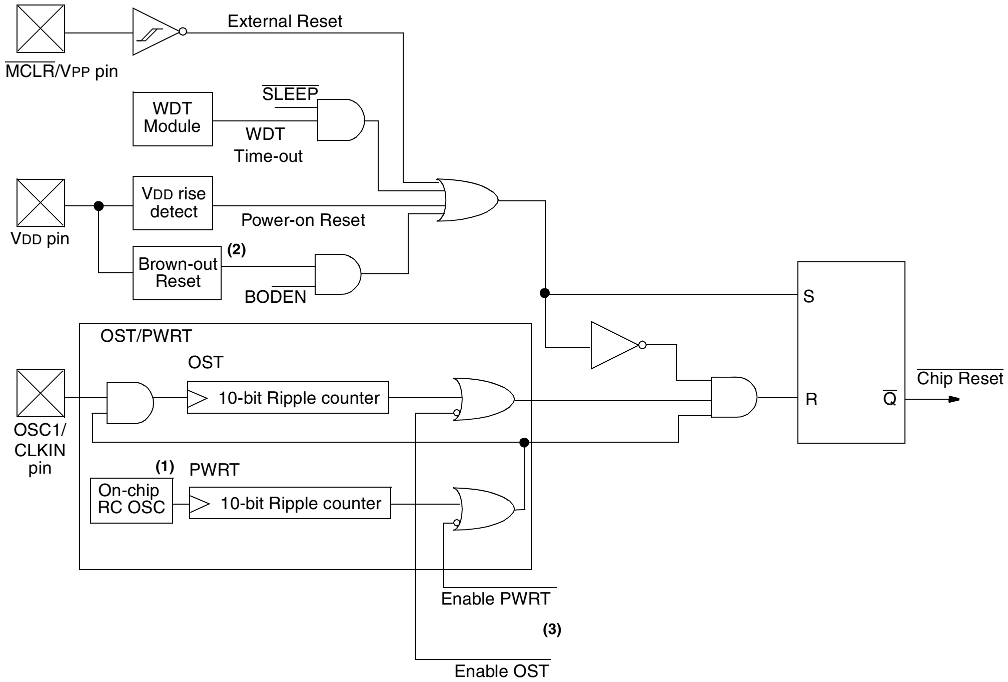
The $\overline{\text{TO}}$ and $\overline{\text{PD}}$ bits are set or cleared differently in different reset situations as indicated in Table 13-7, Table 13-8, and Table 13-9. These bits are used in software to determine the nature of the reset. See Table 13-12 for a full description of reset states of all registers.

A simplified block diagram of the on-chip reset circuit is shown in Figure 13-9.

On the PIC16C62A/R62/63/R63/64A/R64/65A/R65/66/67, the $\overline{\text{MCLR}}$ reset path has a noise filter to detect and ignore small pulses. See parameter #34 for pulse width specifications.

It should be noted that a WDT Reset does not drive the $\overline{\text{MCLR}}$ pin low.

FIGURE 13-9: SIMPLIFIED BLOCK DIAGRAM OF ON-CHIP RESET CIRCUIT



Note 1: This is a separate oscillator from the RC oscillator of the CLKIN pin.
2: Brown-out Reset is NOT implemented on the PIC16C61/62/64/65.
3: See Table 13-5 and Table 13-6 for time-out situations.

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Applicable Devices	61	62	62A	R62	63	R63	64	64A	R64	65	65A	R65	66	67

FIGURE 15-3: CLKOUT AND I/O TIMING

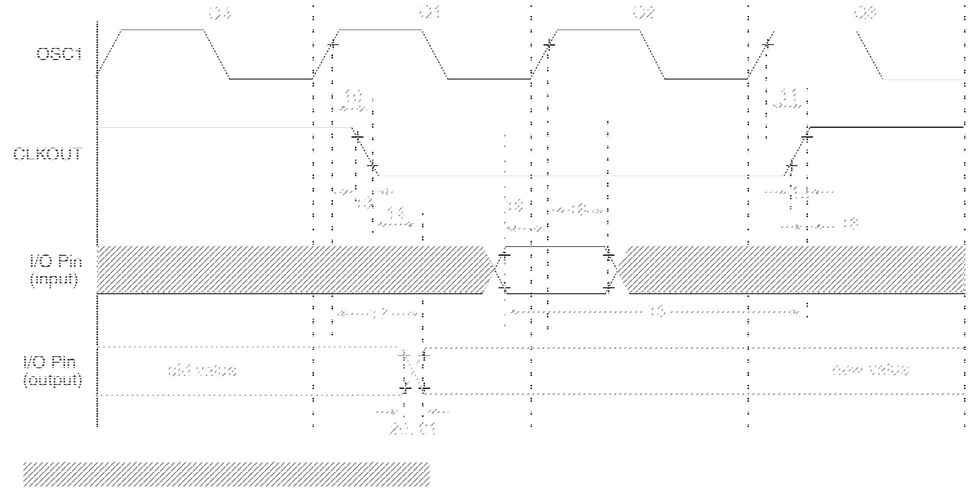

TABLE 15-3: CLKOUT AND I/O TIMING REQUIREMENTS

Parameter No.	Sym	Characteristic		Min	Typ†	Max	Units	Conditions
10*	TosH2ckL	OSC1↑ to CLKOUT↓		—	15	30	ns	Note 1
11*	TosH2ckH	OSC1↑ to CLKOUT↑		—	15	30	ns	Note 1
12*	TckR	CLKOUT rise time		—	5	15	ns	Note 1
13*	TckF	CLKOUT fall time		—	5	15	ns	Note 1
14*	TckL2ioV	CLKOUT ↓ to Port out valid		—	—	0.5TCY + 20	ns	Note 1
15*	TioV2ckH	Port in valid before CLKOUT ↑		0.25TCY + 25	—	—	ns	Note 1
16*	TckH2ioI	Port in hold after CLKOUT ↑		0	—	—	ns	Note 1
17*	TosH2ioV	OSC1↑ (Q1 cycle) to Port out valid		—	—	80 - 100	ns	
18*	TosH2ioI	OSC1↑ (Q2 cycle) to Port input invalid (I/O in hold time)		TBD	—	—	ns	
19*	TioV2osH	Port input valid to OSC1↑ (I/O in setup time)		TBD	—	—	ns	
20*	TioR	Port output rise time	PIC16**C**61	—	10	25	ns	
			PIC16**LC**61	—	—	60	ns	
21*	TioF	Port output fall time	PIC16**C**61	—	10	25	ns	
			PIC16**LC**61	—	—	60	ns	
22††*	Tinp	RB0/INT pin high or low time		20	—	—	ns	
23††*	Trbp	RB7:RB4 change int high or low time		20	—	—	ns	

* These parameters are characterized but not tested.

† Data in "Typ" column is at 5V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

†† These parameters are asynchronous events not related to any internal clock edges.

Note 1: Measurements are taken in RC Mode where CLKOUT output is 4 x TOSC.

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FIGURE 16-6: TYPICAL IPD VS. VDD WATCHDOG TIMER ENABLED 25°C

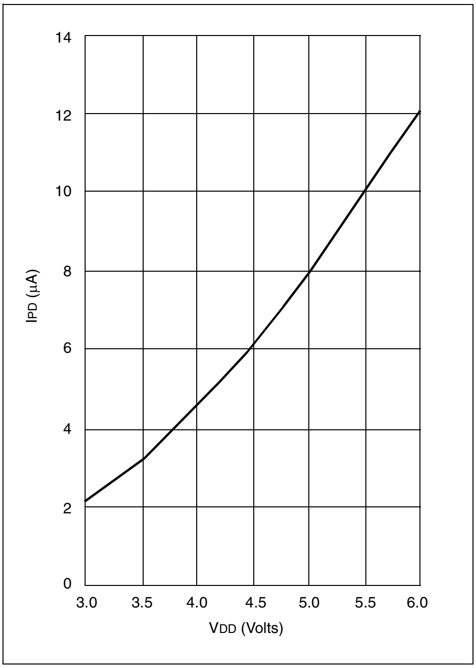
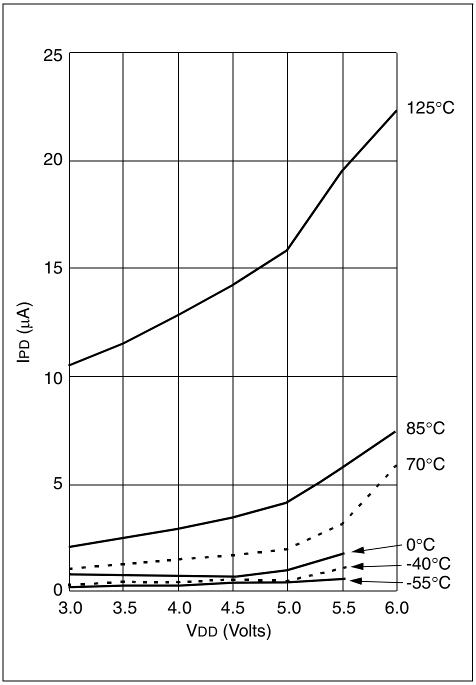


FIGURE 16-7: MAXIMUM IPD VS. VDD WATCHDOG DISABLED



Data based on matrix samples. See first page of this section for details.

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17.0 ELECTRICAL CHARACTERISTICS FOR PIC16C62/64

Absolute Maximum Ratings †

Ambient temperature under bias	-55°C to +85°C
Storage temperature	-65°C to +150°C
Voltage on any pin with respect to VSS (except VDD, $\overline{\text{MCLR}}$, and RA4)	-0.3V to (VDD + 0.3V)
Voltage on VDD with respect to VSS	-0.3V to +7.5V
Voltage on $\overline{\text{MCLR}}$ with respect to VSS (Note 2)	0V to +14V
Voltage on RA4 with respect to Vss	0V to +14V
Total power dissipation (Note 1)	1.0W
Maximum current out of VSS pin	300 mA
Maximum current into VDD pin	250 mA
Input clamp current, IIK (VI < 0 or VI > VDD)	±20 mA
Output clamp current, IOK (VO < 0 or VO > VDD)	±20 mA
Maximum output current sunk by any I/O pin	25 mA
Maximum output current sourced by any I/O pin	25 mA
Maximum current sunk by PORTA, PORTB, and PORTE* (combined)	200 mA
Maximum current sourced by PORTA, PORTB, and PORTE* (combined)	200 mA
Maximum current sunk by PORTC and PORTD* (combined)	200 mA
Maximum current sourced by PORTC and PORTD* (combined)	200 mA

* PORTD and PORTE not available on the PIC16C62.

Note 1: Power dissipation is calculated as follows: $P_{dis} = V_{DD} \times \{I_{DD} - \sum I_{OH}\} + \sum \{(V_{DD}-V_{OH}) \times I_{OH}\} + \sum(V_{Ol} \times I_{OL})$

Note 2: Voltage spikes below VSS at the $\overline{\text{MCLR}}$ pin, inducing currents greater than 80 mA, may cause latch-up. Thus, a series resistor of 50-100Ω should be used when applying a "low" level to the $\overline{\text{MCLR}}$ pin rather than pulling this pin directly to VSS.

† NOTICE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

TABLE 17-1: CROSS REFERENCE OF DEVICE SPECS FOR OSCILLATOR CONFIGURATIONS AND FREQUENCIES OF OPERATION (COMMERCIAL DEVICES)

OSC	PIC16C62-04 PIC16C64-04	PIC16C62-10 PIC16C64-10	PIC16C62-20 PIC16C64-20	PIC16LC62-04 PIC16LC64-04	JW Devices
RC	VDD: 4.0V to 6.0V IDD: 3.8 mA max. at 5.5V IPD: 21 µA max. at 4V Freq:4 MHz max.	VDD: 4.5V to 5.5V IDD: 2.0 mA typ. at 5.5V IPD: 1.5 µA typ. at 4V Freq:4 MHz max.	VDD: 4.5V to 5.5V IDD: 2.0 mA typ. at 5.5V IPD: 1.5 µA typ. at 4V Freq:4 MHz max.	VDD: 3.0V to 6.0V IDD: 3.8 mA max. at 3.0V IPD: 13.5 µA max. at 3V Freq: 4 MHz max.	VDD: 4.0V to 6.0V IDD: 3.8 mA max. at 5.5V IPD: 21 µA max. at 4V Freq:4 MHz max.
XT	VDD: 4.0V to 6.0V IDD: 3.8 mA max. at 5.5V IPD: 21 µA max. at 4V Freq:4 MHz max.	VDD: 4.5V to 5.5V IDD: 2.0 mA typ. at 5.5V IPD: 1.5 µA typ. at 4V Freq:4 MHz max.	VDD: 4.5V to 5.5V IDD: 2.0 mA typ. at 5.5V IPD: 1.5 µA typ. at 4V Freq:4 MHz max.	VDD: 3.0V to 6.0V IDD: 3.8 mA max. at 3.0V IPD: 13.5 µA max. at 3.0V Freq: 4 MHz max.	VDD: 4.0V to 6.0V IDD: 3.8 mA max. at 5.5V IPD: 21 µA max. at 4V Freq:4 MHz max.
HS	VDD: 4.5V to 5.5V IDD: 13.5 mA typ. at 5.5V IPD: 1.5 µA typ. at 4.5V Freq:4 MHz max.	VDD: 4.5V to 5.5V IDD: 15 mA max. at 5.5V IPD: 1.5 µA typ. at 4.5V Freq: 10 MHz max.	VDD: 4.5V to 5.5V IDD: 30 mA max. at 5.5V IPD: 1.5 µA typ. at 4.5V Freq: 20 MHz max.	Not recommended for use in HS mode	VDD: 4.5V to 5.5V IDD: 30 mA max. at 5.5V IPD: 1.5 µA typ. at 4.5V Freq: 20 MHz max.
LP	VDD: 4.0V to 6.0V IDD: 52.5 µA typ. at 32 kHz, 4.0V IPD: 0.9 µA typ. at 4.0V Freq:200 kHz max.	Not recommended for use in LP mode	Not recommended for use in LP mode	VDD: 3.0V to 6.0V IDD: 48 µA max. at 32 kHz, 3.0V IPD: 13.5 µA max. at 3.0V Freq:200 kHz max.	VDD: 3.0V to 6.0V IDD: 48 µA max. at 32 kHz, 3.0V IPD:13.5 µA max. at 3.0V Freq:200 kHz max.

The shaded sections indicate oscillator selections which are tested for functionality, but not for MIN/MAX specifications. It is recommended that the user select the device type that ensures the specifications required.

Applicable Devices	61	62	62A	R62	63	R63	64	64A	R64	65	65A	R65	66	67

17.2 DC Characteristics: PIC16LC62/64-04 (Commercial, Industrial)

DC CHARACTERISTICS	Standard Operating Conditions (unless otherwise stated) Operating temperature -40°C ≤ TA ≤ +85°C for industrial and 0°C ≤ TA ≤ +70°C for commercial						
Param No.	**Characteristic**	**Sym**	**Min**	**Typ†**	**Max**	**Units**	**Conditions**
D001	Supply Voltage	VDD	3.0	-	6.0	V	LP, XT, RC osc configuration (DC - 4 MHz)
D002*	RAM Data Retention Voltage (Note 1)	VDR	-	1.5	-	V	
D003	VDD start voltage to ensure internal Power-on Reset signal	VPOR	-	VSS	-	V	See section on Power-on Reset for details
D004*	VDD rise rate to ensure internal Power-on Reset signal	SVDD	0.05	-	-	V/ms	See section on Power-on Reset for details
D010	Supply Current (Note 2, 5)	IDD	-	2.0	3.8	mA	XT, RC osc configuration FOSC = 4 MHz, VDD = 3.0V (Note 4)
D010A			-	22.5	48	µA	LP osc configuration FOSC = 32 kHz, VDD = 3.0V, WDT disabled
D020	Power-down Current (Note 3, 5)	IPD	-	7.5	30	µA	VDD = 3.0V, WDT enabled, -40°C to +85°C
D021			-	0.9	13.5	µA	VDD = 3.0V, WDT disabled, 0°C to +70°C
D021A			-	0.9	18	µA	VDD = 3.0V, WDT disabled, -40°C to +85°C

* These parameters are characterized but not tested.

† Data in "Typ" column is at 5V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

Note 1: This is the limit to which VDD can be lowered without losing RAM data.

2: The supply current is mainly a function of the operating voltage and frequency. Other factors such as I/O pin loading and switching rate, oscillator type, internal code execution pattern, and temperature also have an impact on the current consumption.
The test conditions for all IDD measurements in active operation mode are:
OSC1 = external square wave, from rail to rail; all I/O pins tristated, pulled to VDD
$\overline{\text{MCLR}}$ = VDD; WDT enabled/disabled as specified.

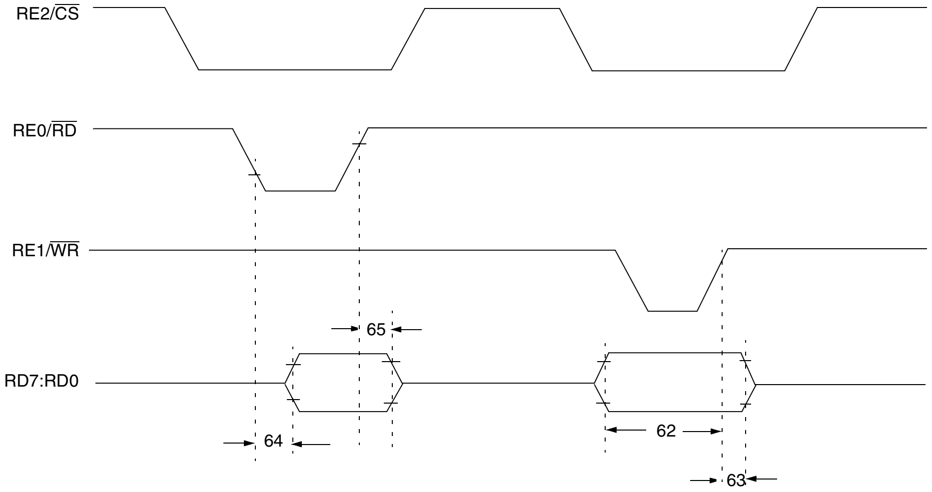
3: The power-down current in SLEEP mode does not depend on the oscillator type. Power-down current is measured with the part in SLEEP mode, with all I/O pins in hi-impedance state and tied to VDD and VSS.

4: For RC osc configuration, current through Rext is not included. The current through the resistor can be estimated by the formula Ir = VDD/2Rext (mA) with Rext in kOhm.

5: Timer1 oscillator (when enabled) adds approximately 20 µA to the specification. This value is from characterization and is for design guidance only. This is not tested.

Applicable Devices	61	62	62A	R62	63	R63	64	64A	R64	65	65A	R65	66	67

FIGURE 19-7: PARALLEL SLAVE PORT TIMING



Note: Refer to Figure 19-1 for load conditions

TABLE 19-7: PARALLEL SLAVE PORT REQUIREMENTS

Parameter No.	Sym	Characteristic		Min	Typ†	Max	Units	Conditions
62	TdtV2wrH	Data in valid before $\overline{\text{WR}}$↑ or $\overline{\text{CS}}$↑ (setup time)		20	—	—	ns	
63*	TwrH2dtI	$\overline{\text{WR}}$↑ or $\overline{\text{CS}}$↑ to data–in invalid (hold time)	PIC16**C**65	20	—	—	ns	
			PIC16**LC**65	35	—	—	ns	
64	TrdL2dtV	$\overline{\text{RD}}$↓ and $\overline{\text{CS}}$↓ to data–out valid		—	—	80	ns	
65	TrdH2dtI	$\overline{\text{RD}}$↑ or $\overline{\text{CS}}$↑ to data–out invalid		10	—	30	ns	

* These parameters are characterized but not tested.

† Data in "Typ" column is at 5V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

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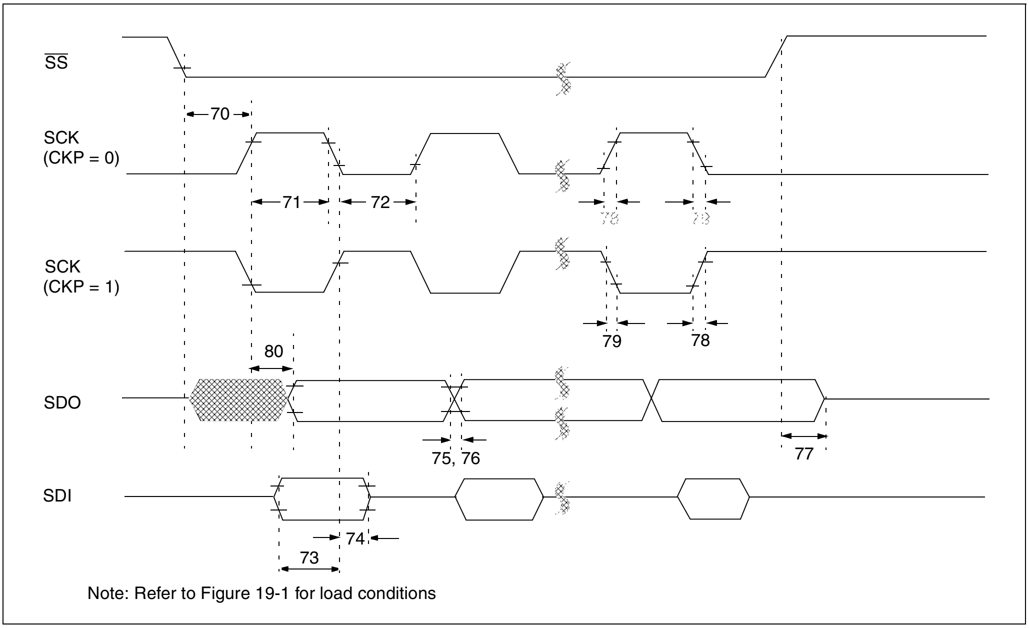
FIGURE 19-8: SPI MODE TIMING



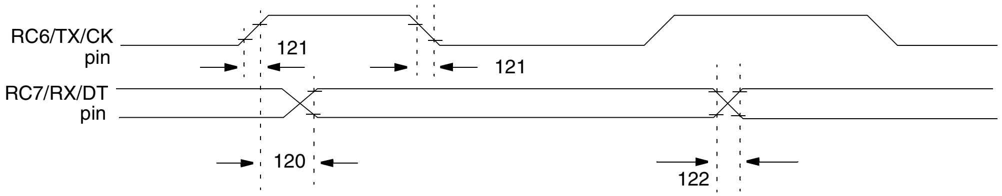
Note: Refer to Figure 19-1 for load conditions

TABLE 19-8: SPI MODE REQUIREMENTS

Parameter No.	Sym	Characteristic	Min	Typ†	Max	Units	Conditions
70	TssL2scH, TssL2scL	$\overline{SS}$↓ to SCK↓ or SCK↑ input	TCY	—	—	ns	
71	TscH	SCK input high time (slave mode)	TCY + 20	—	—	ns	
72	TscL	SCK input low time (slave mode)	TCY + 20	—	—	ns	
73	TdiV2scH, TdiV2scL	Setup time of SDI data input to SCK edge	50	—	—	ns	
74	TscH2diL, TscL2diL	Hold time of SDI data input to SCK edge	50	—	—	ns	
75	TdoR	SDO data output rise time	—	10	25	ns	
76	TdoF	SDO data output fall time	—	10	25	ns	
77	TssH2doZ	$\overline{SS}$↑ to SDO output hi-impedance	10	—	50	ns	
78	TscR	SCK output rise time (master mode)	—	10	25	ns	
79	TscF	SCK output fall time (master mode)	—	10	25	ns	
80	TscH2doV, TscL2doV	SDO data output valid after SCK edge	—	—	50	ns	

† Data in "Typ" column is at 5V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

FIGURE 19-11: USART SYNCHRONOUS TRANSMISSION (MASTER/SLAVE) TIMING



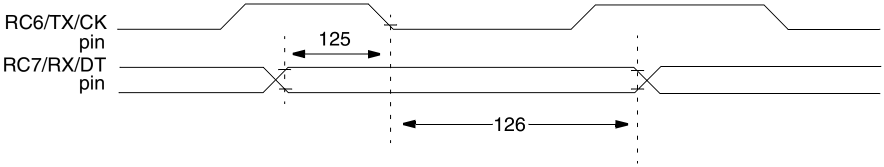
Note: Refer to Figure 19-1 for load conditions

TABLE 19-11: USART SYNCHRONOUS TRANSMISSION REQUIREMENTS

Parameter No.	Sym	Characteristic		Min	Typ†	Max	Units	Conditions
120	TckH2dtV	<u>SYNC XMIT (MASTER & SLAVE)</u> Clock high to data out valid	PIC16**C**65	—	—	80	ns	
			PIC16**LC**65	—	—	100	ns	
121	Tckrf	Clock out rise time and fall time (Master Mode)	PIC16**C**65	—	—	45	ns	
			PIC16**LC**65	—	—	50	ns	
122	Tdtrf	Data out rise time and fall time	PIC16**C**65	—	—	45	ns	
			PIC16**LC**65	—	—	50	ns	

†: Data in “Typ” column is at 5V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

FIGURE 19-12: USART SYNCHRONOUS RECEIVE (MASTER/SLAVE) TIMING



Note: Refer to Figure 19-1 for load conditions

TABLE 19-12: USART SYNCHRONOUS RECEIVE REQUIREMENTS

Parameter No.	Sym	Characteristic	Min	Typ†	Max	Units	Conditions
125	TdtV2ckL	<u>SYNC RCV (MASTER & SLAVE)</u> Data setup before CK ↓ (DT setup time)	15	—	—	ns	
126	TckL2dtl	Data hold after CK ↓ (DT hold time)	15	—	—	ns	

†: Data in “Typ” column is at 5V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

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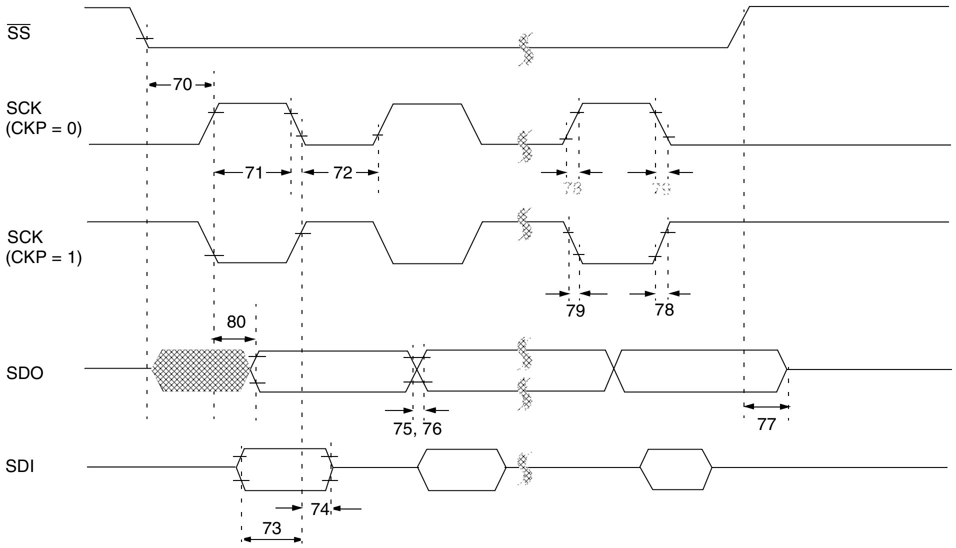
FIGURE 20-9: SPI MODE TIMING



Note: Refer to Figure 20-1 for load conditions

TABLE 20-8: SPI MODE REQUIREMENTS

Parameter No.	Sym	Characteristic	Min	Typ†	Max	Units	Conditions
70*	TssL2scH, TssL2scL	$\overline{SS}$↓ to SCK↓ or SCK↑ input	TCY	—	—	ns	
71*	TscH	SCK input high time (slave mode)	TCY + 20	—	—	ns	
72*	TscL	SCK input low time (slave mode)	TCY + 20	—	—	ns	
73*	TdiV2scH, TdiV2scL	Setup time of SDI data input to SCK edge	50	—	—	ns	
74*	TscH2diL, TscL2diL	Hold time of SDI data input to SCK edge	50	—	—	ns	
75*	TdoR	SDO data output rise time	—	10	25	ns	
76*	TdoF	SDO data output fall time	—	10	25	ns	
77*	TssH2doZ	$\overline{SS}$↑ to SDO output hi-impedance	10	—	50	ns	
78*	TscR	SCK output rise time (master mode)	—	10	25	ns	
79*	TscF	SCK output fall time (master mode)	—	10	25	ns	
80*	TscH2doV, TscL2doV	SDO data output valid after SCK edge	—	—	50	ns	

* These parameters are characterized but not tested.

† Data in "Typ" column is at 5V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

Applicable Devices	61	62	62A	R62	63	R63	64	64A	R64	65	65A	R65	66	67

21.0 ELECTRICAL CHARACTERISTICS FOR PIC16CR63/R65

Absolute Maximum Ratings (†)

Ambient temperature under bias	-55°C to +125°C
Storage temperature	-65°C to +150°C
Voltage on any pin with respect to V_{SS} (except V_{DD}, $\overline{MCLR}$, and RA4)	-0.3V to (V_{DD} + 0.3V)
Voltage on V_{DD} with respect to V_{SS}	-0.3V to +7.5V
Voltage on $\overline{MCLR}$ with respect to V_{SS} (Note 2)	0V to +14V
Voltage on RA4 with respect to Vss	0V to +14V
Total power dissipation (Note 1)	1.0W
Maximum current out of V_{SS} pin	300 mA
Maximum current into V_{DD} pin	250 mA
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{DD}$)	±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{DD}$)	±20 mA
Maximum output current sunk by any I/O pin	25 mA
Maximum output current sourced by any I/O pin	25 mA
Maximum current sunk by PORTA, PORTB, and PORTE (Note 3) (combined)	200 mA
Maximum current sourced by PORTA, PORTB, and PORTE (Note 3) (combined)	200 mA
Maximum current sunk by PORTC and PORTD (Note 3) (combined)	200 mA
Maximum current sourced by PORTC and PORTD (Note 3) (combined)	200 mA

Note 1: Power dissipation is calculated as follows: $P_{dis} = V_{DD} \times \{I_{DD} - \sum I_{OH}\} + \sum \{(V_{DD}-V_{OH}) \times I_{OH}\} + \sum(V_{Ol} \times I_{OL})$

Note 2: Voltage spikes below V_{SS} at the $\overline{MCLR}$/V_{PP} pin, inducing currents greater than 80 mA, may cause latch-up. Thus, a series resistor of 50-100Ω should be used when applying a “low” level to the $\overline{MCLR}$/V_{PP} pin rather than pulling this pin directly to V_{SS}.

Note 3: PORTD and PORTE not available on the PIC16CR63.

† NOTICE: Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

PRELIMINARY

TABLE 21-1: CROSS REFERENCE OF DEVICE SPECS FOR OSCILLATOR CONFIGURATIONS AND FREQUENCIES OF OPERATION (COMMERCIAL DEVICES)

OSC	PIC16CR63-04 PIC16CR65-04	PIC16CR63-10 PIC16CR65-10	PIC16CR63-20 PIC16CR65-20	PIC16LCR63-04 PIC16LCR65-04	JW Devices
RC	V_{DD}: 4.0V to 5.5V I_{DD}: 5 mA max. at 5.5V I_{PD}: 16 μA max. at 4V Freq: 4 MHz max.	V_{DD}: 4.5V to 5.5V I_{DD}: 2.7 mA typ. at 5.5V I_{PD}: 1.5 μA typ. at 4V Freq: 4 MHz max.	V_{DD}: 4.5V to 5.5V I_{DD}: 2.7 mA typ. at 5.5V I_{PD}: 1.5 μA typ. at 4V Freq: 4 MHz max.	V_{DD}: 3.0V to 5.5V I_{DD}: 3.8 mA max. at 3V I_{PD}: 5 μA max. at 3V Freq: 4 MHz max.	V_{DD}: 4.0V to 5.5V I_{DD}: 5 mA max. at 5.5V I_{PD}: 16 μA max. at 4V Freq: 4 MHz max.
XT	V_{DD}: 4.0V to 5.5V I_{DD}: 5 mA max. at 5.5V I_{PD}: 16 μA max. at 4V Freq: 4 MHz max.	V_{DD}: 4.5V to 5.5V I_{DD}: 2.7 mA typ. at 5.5V I_{PD}: 1.5 μA typ. at 4V Freq: 4 MHz max.	V_{DD}: 4.5V to 5.5V I_{DD}: 2.7 mA typ. at 5.5V I_{PD}: 1.5 μA typ. at 4V Freq: 4 MHz max.	V_{DD}: 3.0V to 5.5V I_{DD}: 3.8 mA max. at 3V I_{PD}: 5 μA max. at 3V Freq: 4 MHz max.	V_{DD}: 4.0V to 5.5V I_{DD}: 5 mA max. at 5.5V I_{PD}: 16 μA max. at 4V Freq: 4 MHz max.
HS	V_{DD}: 4.5V to 5.5V I_{DD}: 13.5 mA typ. at 5.5V I_{PD}: 1.5 μA typ. at 4.5V Freq: 4 MHz max.	V_{DD}: 4.5V to 5.5V I_{DD}: 10 mA max. at 5.5V I_{PD} 1.5 μA typ. at 4.5V Freq: 10 MHz max.	V_{DD}: 4.5V to 5.5V I_{DD}: 20 mA max. at 5.5V I_{PD}: 1.5 μA typ. at 4.5V Freq: 20 MHz max.	Not recommended for use in HS mode	V_{DD}: 4.5V to 5.5V I_{DD}: 20 mA max. at 5.5V I_{PD}: 1.5 μA typ. at 4.5V Freq: 20 MHz max.
LP	V_{DD}: 4.0V to 5.5V I_{DD}: 52.5 μA typ. at 32 kHz, 4.0V I_{PD}: 0.9 μA typ. at 4.0V Freq: 200 kHz max.	Not recommended for use in LP mode	Not recommended for use in LP mode	V_{DD}: 3.0V to 5.5V I_{DD}: 48 μA max. at 32 kHz, 3.0V I_{PD}: 5 μA max. at 3.0V Freq: 200 kHz max.	V_{DD}: 3.0V to 5.5V I_{DD}: 48 μA max. at 32 kHz, 3.0V I_{PD}: 5 μA max. at 3.0V Freq: 200 kHz max.

The shaded sections indicate oscillator selections which are tested for functionality, but not for MIN/MAX specifications. It is recommended that the user select the device type that ensures the specifications required.

22.2 DC Characteristics: PIC16LC66/67-04 (Commercial, Industrial)

DC CHARACTERISTICS		**Standard Operating Conditions (unless otherwise stated)** Operating temperature -40°C ≤ TA ≤ +85°C for industrial and 0°C ≤ TA ≤ +70°C for commercial					
Param No.	**Characteristic**	**Sym**	**Min**	**Typ†**	**Max**	**Units**	**Conditions**
D001	Supply Voltage	VDD	2.5	-	6.0	V	LP, XT, RC osc configuration (DC - 4 MHz)
D002*	RAM Data Retention Voltage (Note 1)	VDR	-	1.5	-	V	
D003	VDD start voltage to ensure internal Power-on Reset signal	VPOR	-	VSS	-	V	See section on Power-on Reset for details
D004*	VDD rise rate to ensure internal Power-on Reset signal	SVDD	0.05	-	-	V/ms	See section on Power-on Reset for details
D005	Brown-out Reset Voltage	BVDD	3.7	4.0	4.3	V	BODEN configuration bit is enabled
D010	Supply Current (Note 2, 5)	IDD	-	2.0	3.8	mA	XT, RC osc configuration FOSC = 4 MHz, VDD = 3.0V (Note 4)
D010A			-	22.5	48	µA	LP osc configuration FOSC = 32 kHz, VDD = 3.0V, WDT disabled
D015*	Brown-out Reset Current (Note 6)	ΔIBOR	-	350	425	µA	BOR enabled, VDD = 5.0V
D020	Power-down Current (Note 3, 5)	IPD	-	7.5	30	µA	VDD = 3.0V, WDT enabled, -40°C to +85°C
D021			-	0.9	5	µA	VDD = 3.0V, WDT disabled, 0°C to +70°C
D021A			-	0.9	5	µA	VDD = 3.0V, WDT disabled, -40°C to +85°C
D023*	Brown-out Reset Current (Note 6)	ΔIBOR	-	350	425	µA	BOR enabled, VDD = 5.0V

* These parameters are characterized but not tested.

† Data in "Typ" column is at 5V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

Note 1: This is the limit to which VDD can be lowered without losing RAM data.

2: The supply current is mainly a function of the operating voltage and frequency. Other factors such as I/O pin loading and switching rate, oscillator type, internal code execution pattern, and temperature also have an impact on the current consumption.
The test conditions for all IDD measurements in active operation mode are:
OSC1 = external square wave, from rail to rail; all I/O pins tristated, pulled to VDD,
$\overline{\text{MCLR}}$ = VDD; WDT enabled/disabled as specified.

3: The power-down current in SLEEP mode does not depend on the oscillator type. Power-down current is measured with the part in SLEEP mode, with all I/O pins in hi-impedance state and tied to VDD and VSS.

4: For RC osc configuration, current through Rext is not included. The current through the resistor can be estimated by the formula Ir = VDD/2Rext (mA) with Rext in kOhm.

5: Timer1 oscillator (when enabled) adds approximately 20 µA to the specification. This value is from characterization and is for design guidance only. This is not tested.

6: The Δ current is the additional current consumed when this peripheral is enabled. This current should be added to the base IDD or IPD measurement.

Applicable Devices	61	62	62A	R62	63	R63	64	64A	R64	65	65A	R65	66	67

FIGURE 23-16: TYPICAL IDD vs. FREQUENCY (RC MODE @ 300 pF, 25°C)

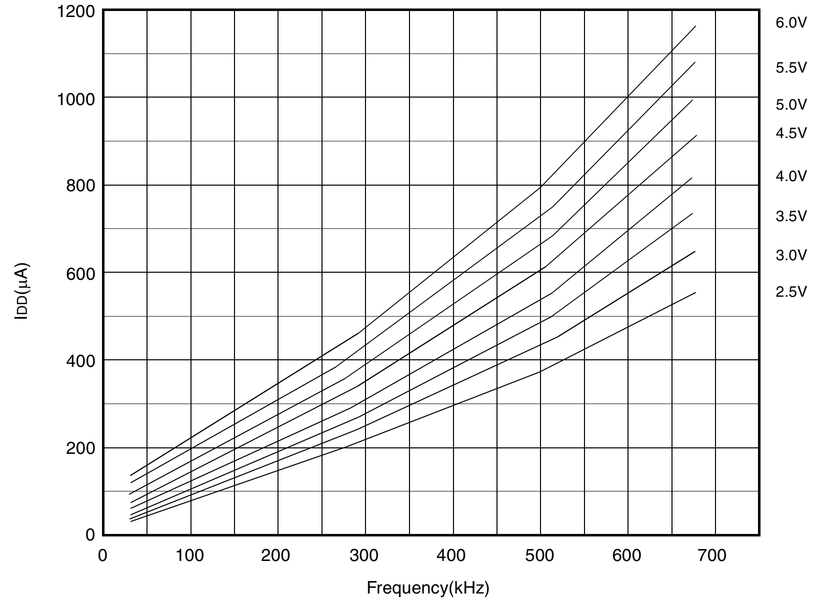
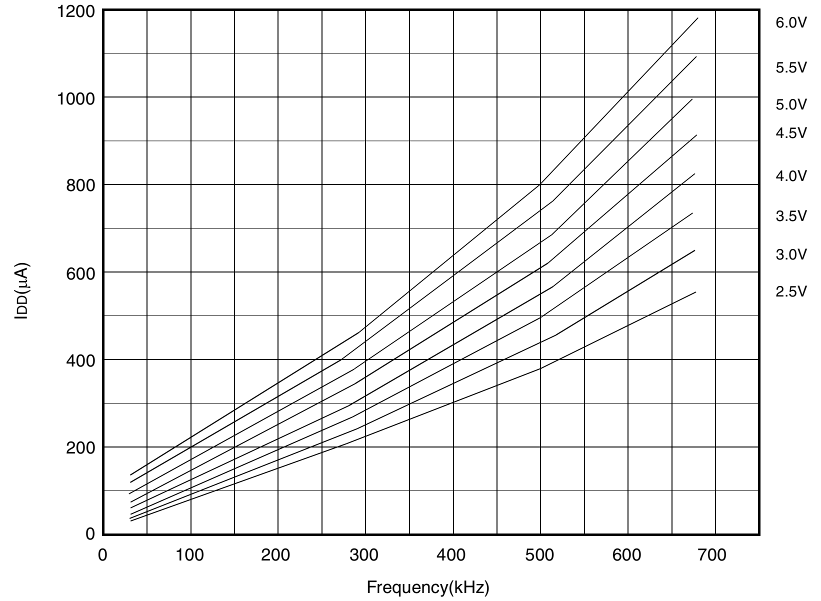


FIGURE 23-17: MAXIMUM IDD vs. FREQUENCY (RC MODE @ 300 pF, -40°C TO 85°C)



Data based on matrix samples. See first page of this section for details.

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FIGURE 23-18: TYPICAL IDD vs. CAPACITANCE @ 500 kHz (RC MODE)

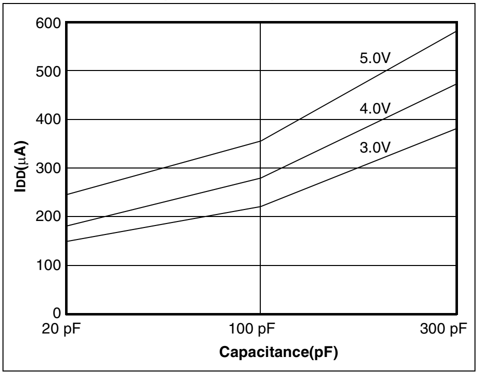
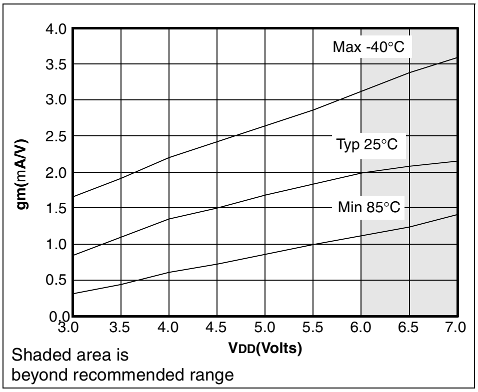


TABLE 23-1: RC OSCILLATOR FREQUENCIES

Cext	Rext	Average	
		Fosc @ 5V, 25°C	
22 pF	5k	4.12 MHz	± 1.4%
	10k	2.35 MHz	± 1.4%
	100k	268 kHz	± 1.1%
100 pF	3.3k	1.80 MHz	± 1.0%
	5k	1.27 MHz	± 1.0%
	10k	688 kHz	± 1.2%
	100k	77.2 kHz	± 1.0%
300 pF	3.3k	707 kHz	± 1.4%
	5k	501 kHz	± 1.2%
	10k	269 kHz	± 1.6%
	100k	28.3 kHz	± 1.1%

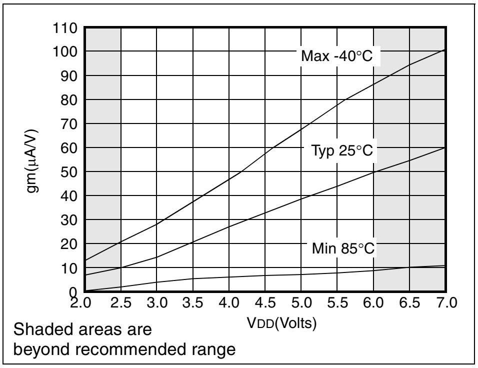
The percentage variation indicated here is part to part variation due to normal process distribution. The variation indicated is ±3 standard deviation from average value for VDD = 5V.

FIGURE 23-19: TRANSCONDUCTANCE(gm) OF HS OSCILLATOR vs. VDD



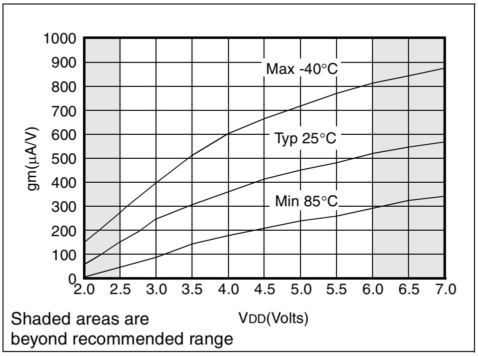
Shaded area is beyond recommended range

FIGURE 23-20: TRANSCONDUCTANCE(gm) OF LP OSCILLATOR vs. VDD



Shaded areas are beyond recommended range

FIGURE 23-21: TRANSCONDUCTANCE(gm) OF XT OSCILLATOR vs. VDD



Shaded areas are beyond recommended range

Data based on matrix samples. See first page of this section for details.

Applicable Devices	61	62	62A	R62	63	R63	64	64A	R64	65	65A	R65	66	67

FIGURE 23-29: TYPICAL I_{DD} vs. FREQUENCY (HS MODE, 25°C)

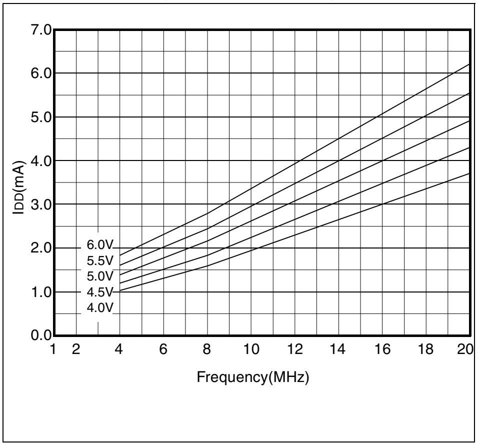
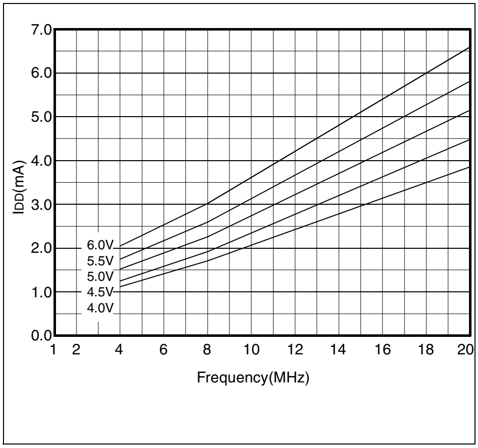


FIGURE 23-30: MAXIMUM I_{DD} vs. FREQUENCY (HS MODE, -40°C TO 85°C)



Data based on matrix samples. See first page of this section for details.

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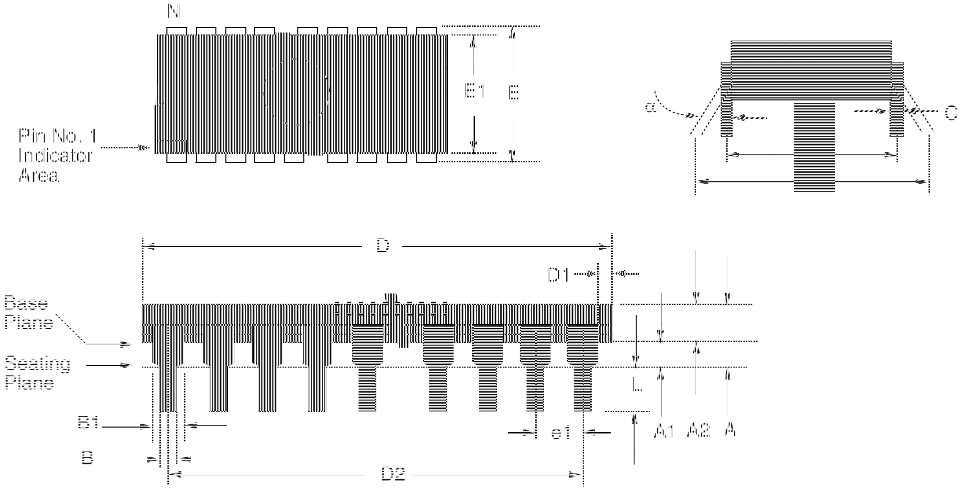
24.7 28-Lead Ceramic CERDIP Dual In-line with Window (300 mil)) (JW)

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Package Group: Ceramic CERDIP Dual In-Line (CDP)						
	Millimeters			Inches		
Symbol	Min	Max	Notes	Min	Max	Notes
α	0°	10°		0°	10°	
A	3.30	5.84		.130	0.230	
A1	0.38	—		0.015	—	
A2	2.92	4.95		0.115	0.195	
B	0.35	0.58		0.014	0.023	
B1	1.14	1.78	**Typical**	0.045	0.070	**Typical**
C	0.20	0.38	**Typical**	0.008	0.015	**Typical**
D	34.54	37.72		1.360	1.485	
D2	32.97	33.07	**Reference**	1.298	1.302	**Reference**
E	7.62	8.25		0.300	0.325	
E1	6.10	7.87		0.240	0.310	
e	2.54	2.54	**Typical**	0.100	0.100	**Typical**
eA	7.62	7.62	**Reference**	0.300	0.300	**Reference**
eB	—	11.43		—	0.450	
L	2.92	5.08		0.115	0.200	
N	28	28		28	28	
D1	0.13	—		0.005	—	

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